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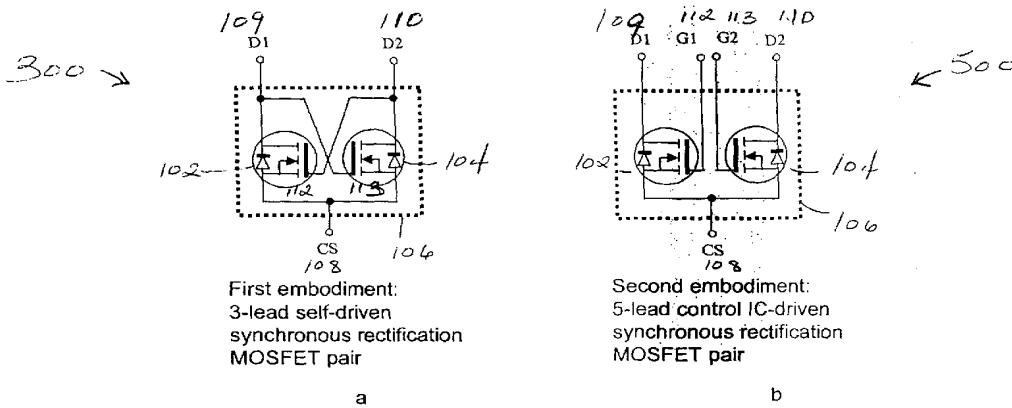
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(54) Title: MONOLITHIC POWER SEMICONDUCTOR STRUCTURES



First embodiment:
3-lead self-driven
synchronous rectification
MOSFET pair

Second embodiment:
5-lead control IC-driven
synchronous rectification
MOSFET pair

a

b

(57) Abstract: Provided herein are exemplary embodiments of monolithic semiconductor structures having at least two lateral constructed semiconductor devices combined on a single semiconductor substrate.

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